CMP150N85/CMB150N85

N-Channel Enhancement Mode Field Effect Transistor

General Description

The 150N85 is a N-channel Power MOSFET. It has specifically been designed to minimize input capacitance and gate charge. The device is therefore suitable in advanced high-efficiency switching applications.

Features

- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

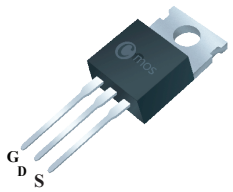
Product Summary

BVDSS	RDSON	ID
85V	6.7mΩ	150A

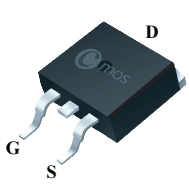
Applications

- LED power controller
- DC-DC & DC-AC converters
- High current, High speed switching
- Solenoid and relay drivers
- Motor control, Audio amplifiers

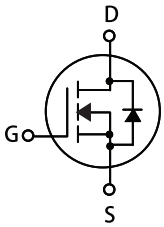
TO-220/263 Pin Configuration



TO-220



TO-263



Type	Package	Marking
CMP150N85	TO-220	CMP150N85
CMB150N85	TO-263	CMB150N85

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	85	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25°C	Continuous Drain Current,VGS @ 10V	150	A
I_D@T_C=100°C	Continuous Drain Current,VGS @ 10V	120	A
I_{DM}	Pulsed Drain Current	600	A
EAS	Single Pulse Avalanche Energy [1]	800	mJ
P_D@T_C=25°C	Power Dissipation	300	W
T_{STG}	Storage Temperature Range	-55 to 175	°C
T_J	Operating Junction Temperature Range	-55 to 175	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)	---	65	°C/W
$R_{\theta JC}$	Junction-to-Case	---	0.5	°C/W

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Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	85	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=20A	---	---	6.7	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=85V, V_{GS}=0V	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V , I_D=20A	---	23	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	2.0	---	Ω
Q_g	Total Gate Charge	I_D=20A V_{DD}=50V V_{GS}=10V	---	106	---	nC
Q_{gs}	Gate-Source Charge		---	28	---	
Q_{gd}	Gate-Drain Charge		---	41	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=50V R_L=2.5Ω R_G=3Ω V_{GS}=10V	---	27	---	ns
T_r	Rise Time		---	21	---	
$T_{d(off)}$	Turn-Off Delay Time		---	43	---	
T_f	Fall Time		---	14	---	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , f=1MHz	---	3500	---	pF
C_{oss}	Output Capacitance		---	1300	---	
C_{rss}	Reverse Transfer Capacitance		---	100	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	150	A
I_{SM}	Pulsed Source Current		---	---	600	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=20A , T_J=25℃	---	---	1.2	V

Note :

1.The EAS data shows Max. rating .The test condition is V_{DS}=50V , V_{GS}=10V , L=1mH , I_{AS}=40A.

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